



BC847QAPN

45 V, 100 mA NPN/PNP general-purpose transistor

19 July 2013

Product data sheet

1. General description

NPN/PNP general-purpose transistor in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Low package height of 0.37 mm

3. Applications

- General-purpose switching and amplification
- Mobile applications

4. Quick reference data

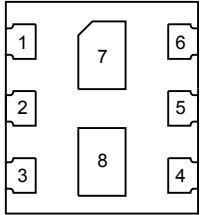
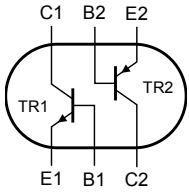
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I_C	collector current		-	-	100	mA
Per transistor; for the PNP transistor with negative polarity						
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}$	200	-	450	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	 <p>Transparent top view DFN1010B-6 (SOT1216)</p>	 <p><i>sym139</i></p>
2	B1	base TR1		
3	C2	collector TR2		
4	E2	emitter TR2		
5	B2	base TR2		
6	C1	collector TR1		
7	C1	collector TR1		
8	C2	collector TR2		

6. Ordering information

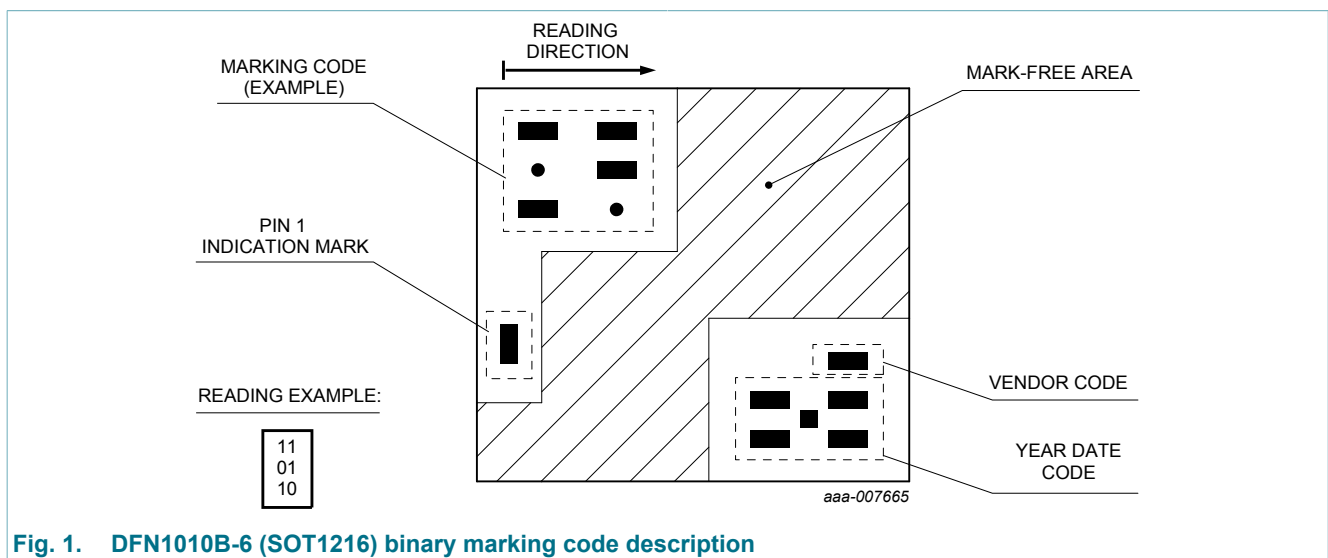
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847QAPN	DFN1010B-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
BC847QAPN	01 00 00



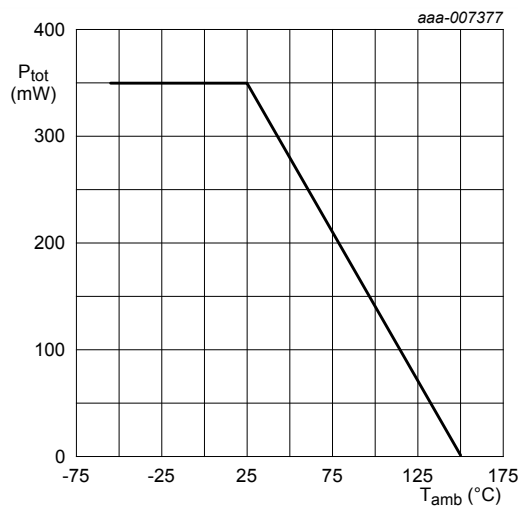
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
V _{CB0}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	200	mA
I _{BM}	peak base current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

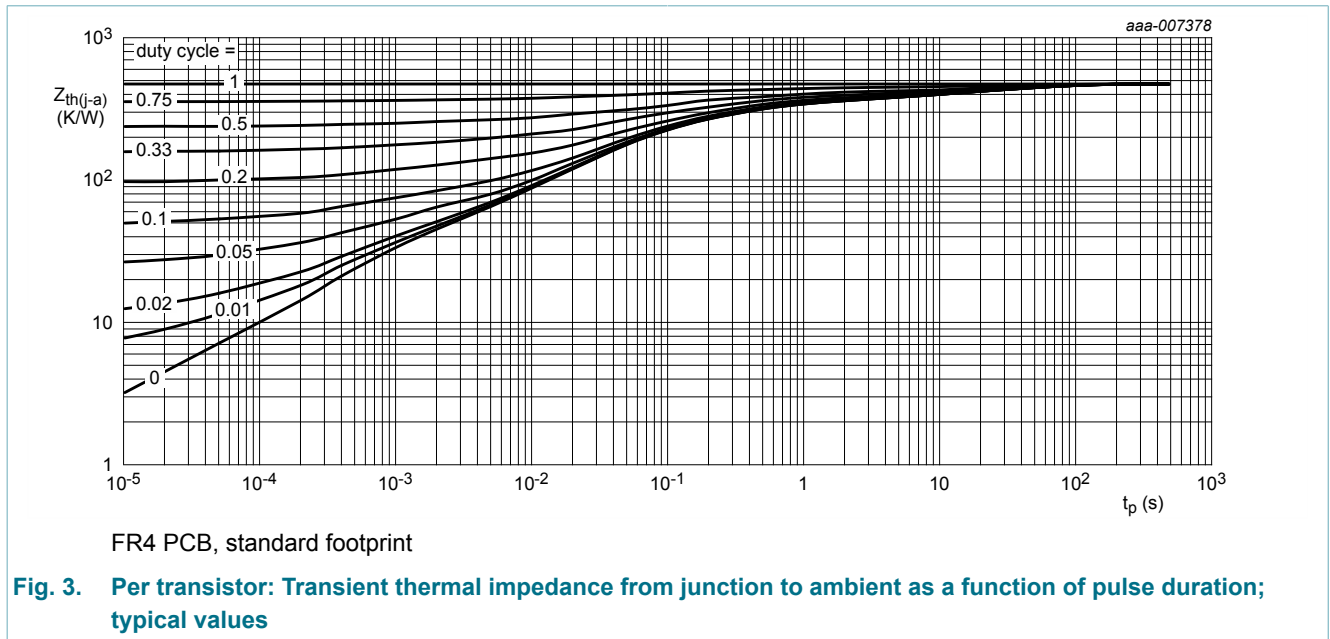
Fig. 2. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor with negative polarity						
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	15	nA
		V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	200	-	450	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	-	100	mV
		I _C = 100 mA; I _B = 5 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	760	-	mV
		I _C = 100 mA; I _B = 5 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	900	-	mV
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C	600	660	725	mV
		V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C	-	710	820	mV
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	4	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
NF	noise figure	V _{CE} = 5 V; I _C = 0.2 mA; R _S = 2 kΩ; f = 1 MHz; B = 200 Hz; T _{amb} = 25 °C	-	-	10	dB
TR1 (NPN)						
C _e	emitter capacitance	V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF
TR2 (PNP)						
C _e	emitter capacitance	V _{EB} = -0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	10	-	pF

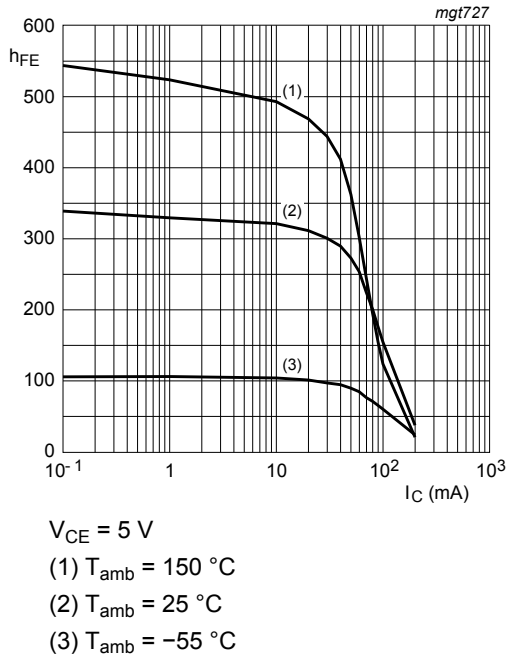


Fig. 4. NPN transistor: DC current gain as a function of collector current; typical values

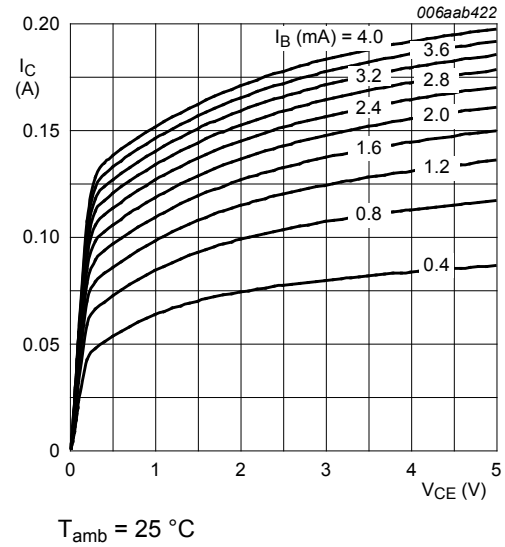


Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

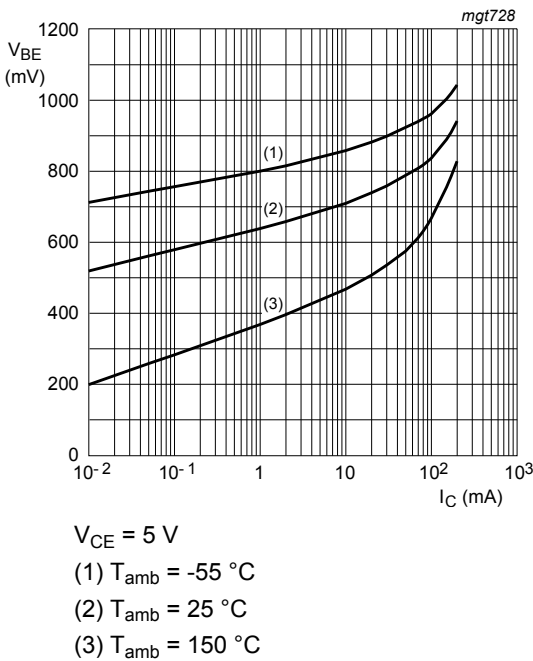


Fig. 6. NPN transistor: Base-emitter voltage as a function of collector current; typical values

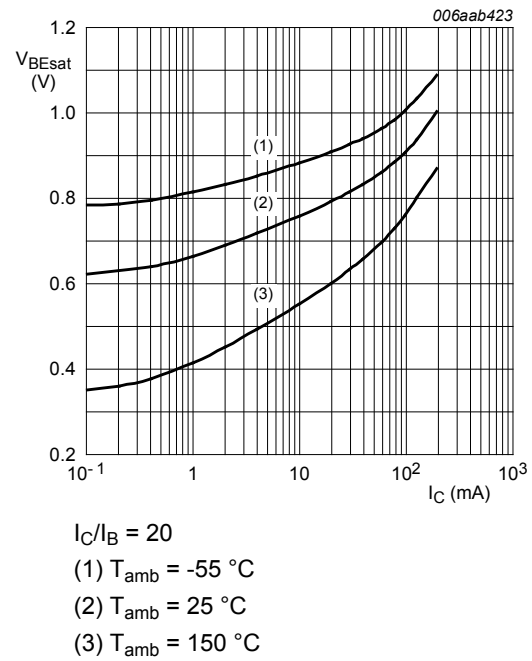
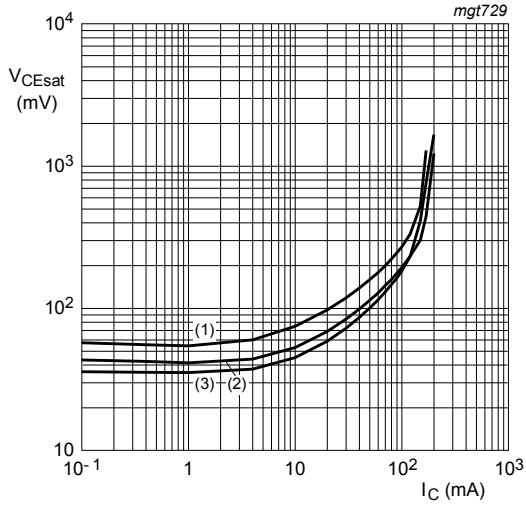
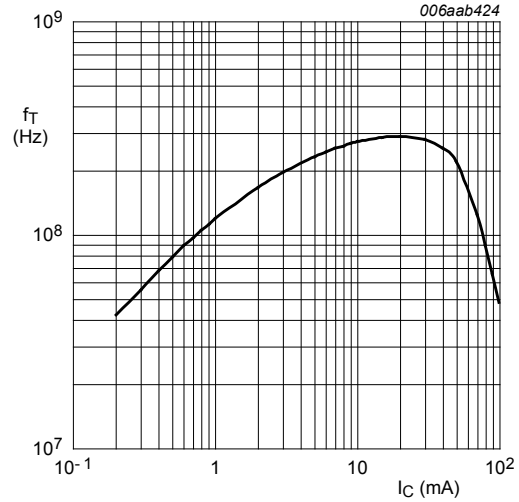


Fig. 7. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



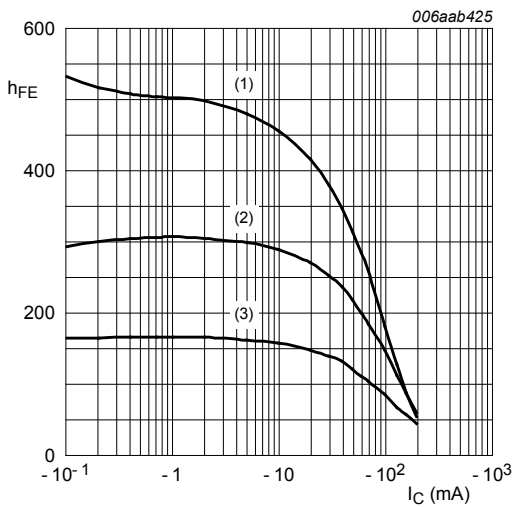
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 8. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



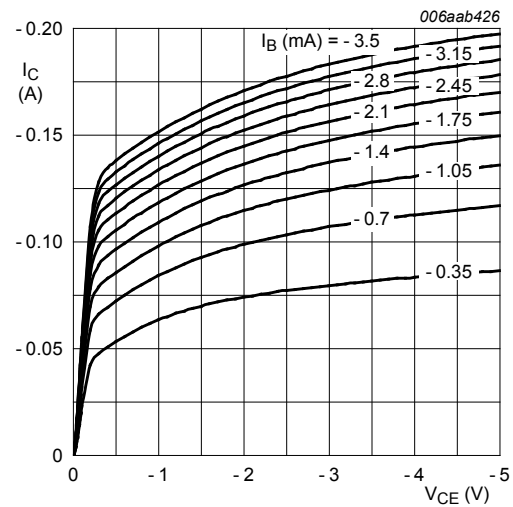
$T_{amb} = 25\text{ }^\circ\text{C};$
 $V_{CE} = 5\text{ V};$
 $f = 100\text{ MHz}$

Fig. 9. Transition frequency as a function of collector current; typical values



$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 150\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values

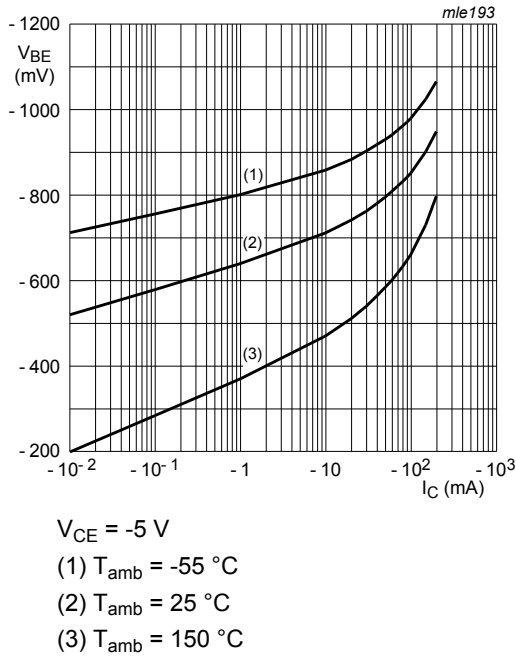


Fig. 12. PNP transistor: Base-emitter voltage as a function of collector current; typical values

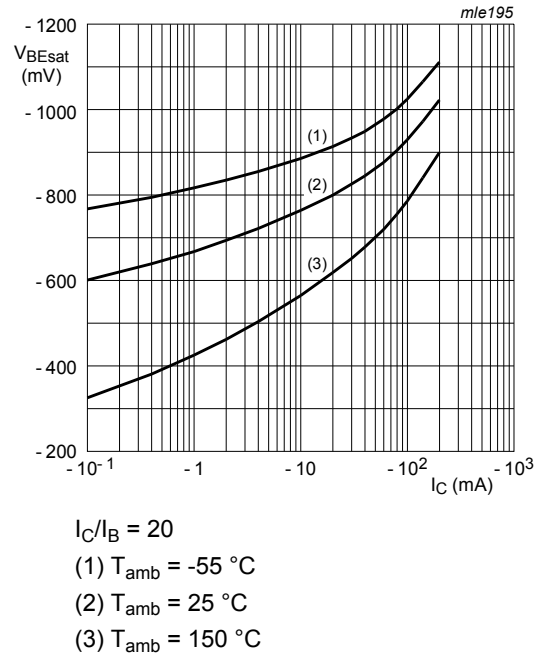


Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

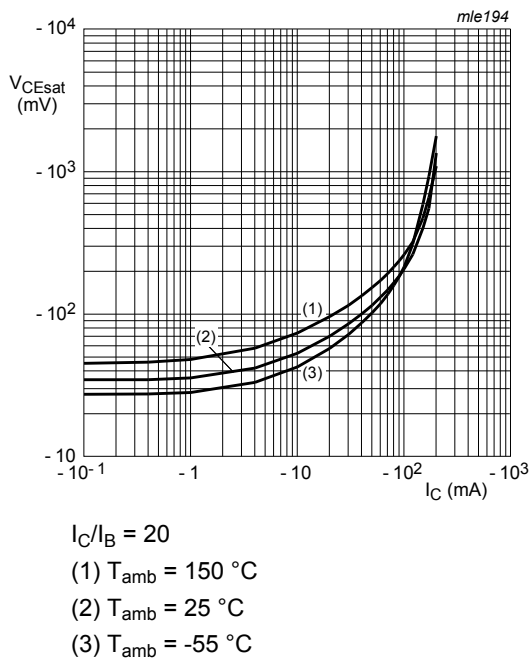


Fig. 14. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

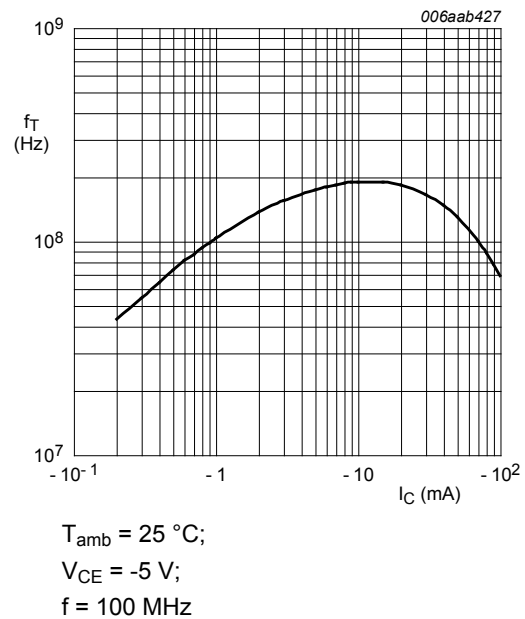


Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

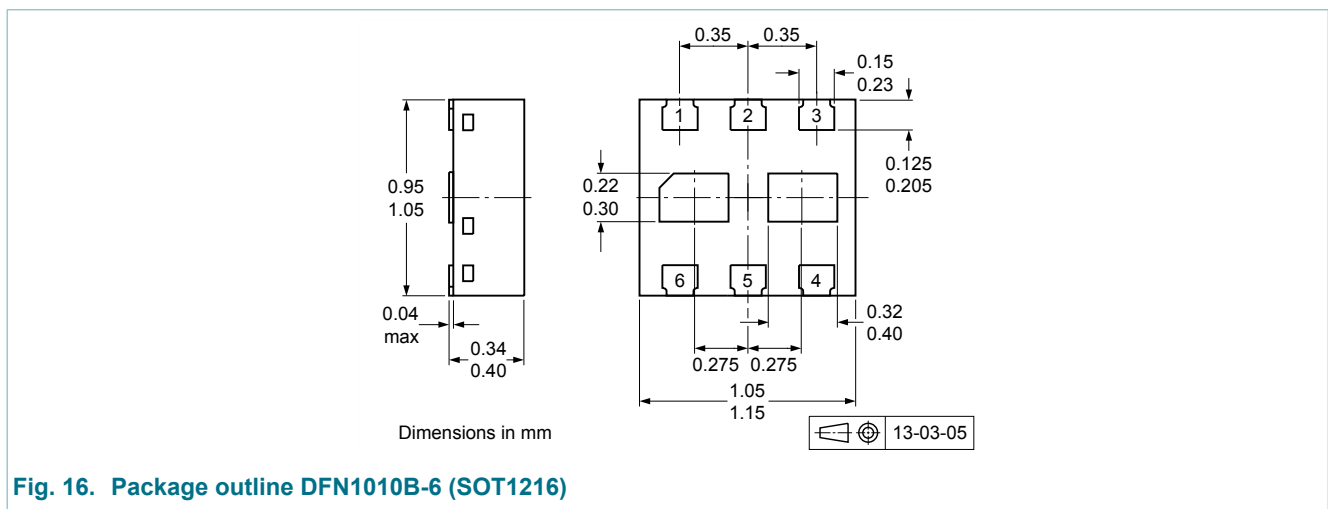


Fig. 16. Package outline DFN1010B-6 (SOT1216)

13. Soldering

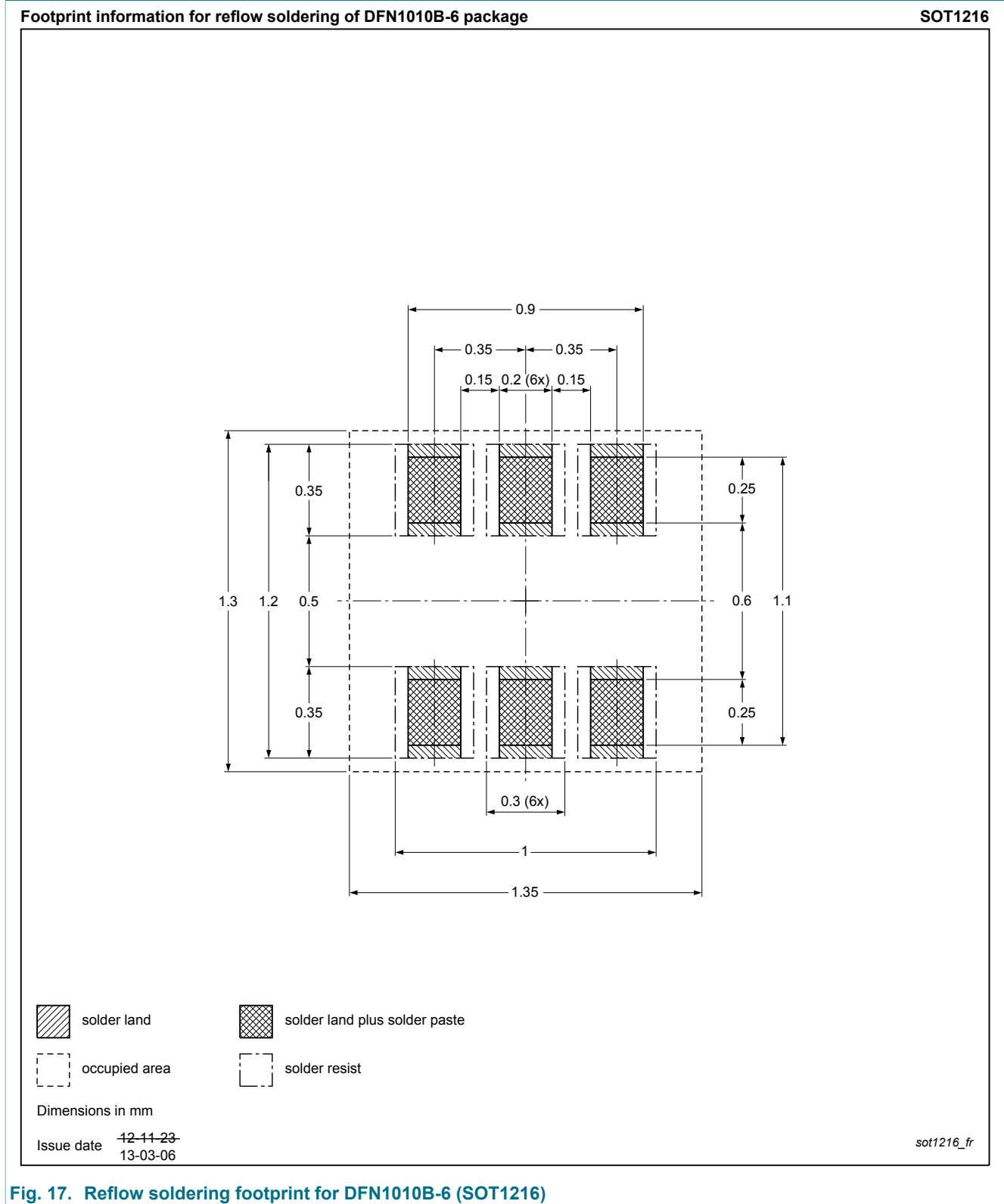


Fig. 17. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847QAPN v.1	20130718	Product data sheet	-	-

45 V, 100 mA NPN/PNP general-purpose transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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